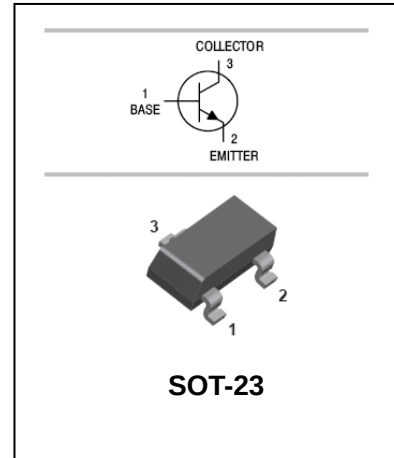


Silicon Epitaxial Planar Transistor

2SC1654

FEATURES

- High DC current gain: $h_{FE}=130$ (Typ)
($V_{CE}=3V, I_C=15mA$)
- High voltage.



APPLICATIONS

- Audio frequency general purpose amplifier applications.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC1654	N5/N6/N7	SOT-23

MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS @ $T_a=25^{\circ}C$ unless otherwise specified

Silicon Epitaxial Planar Transistor**2SC1654**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=130V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=15mA$ $V_{CE}=3V, I_C=5mA$	90 70	200 180	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$		0.1	0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$		0.73	1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA$	120			MHz
Output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1kHz$		2.3		pF

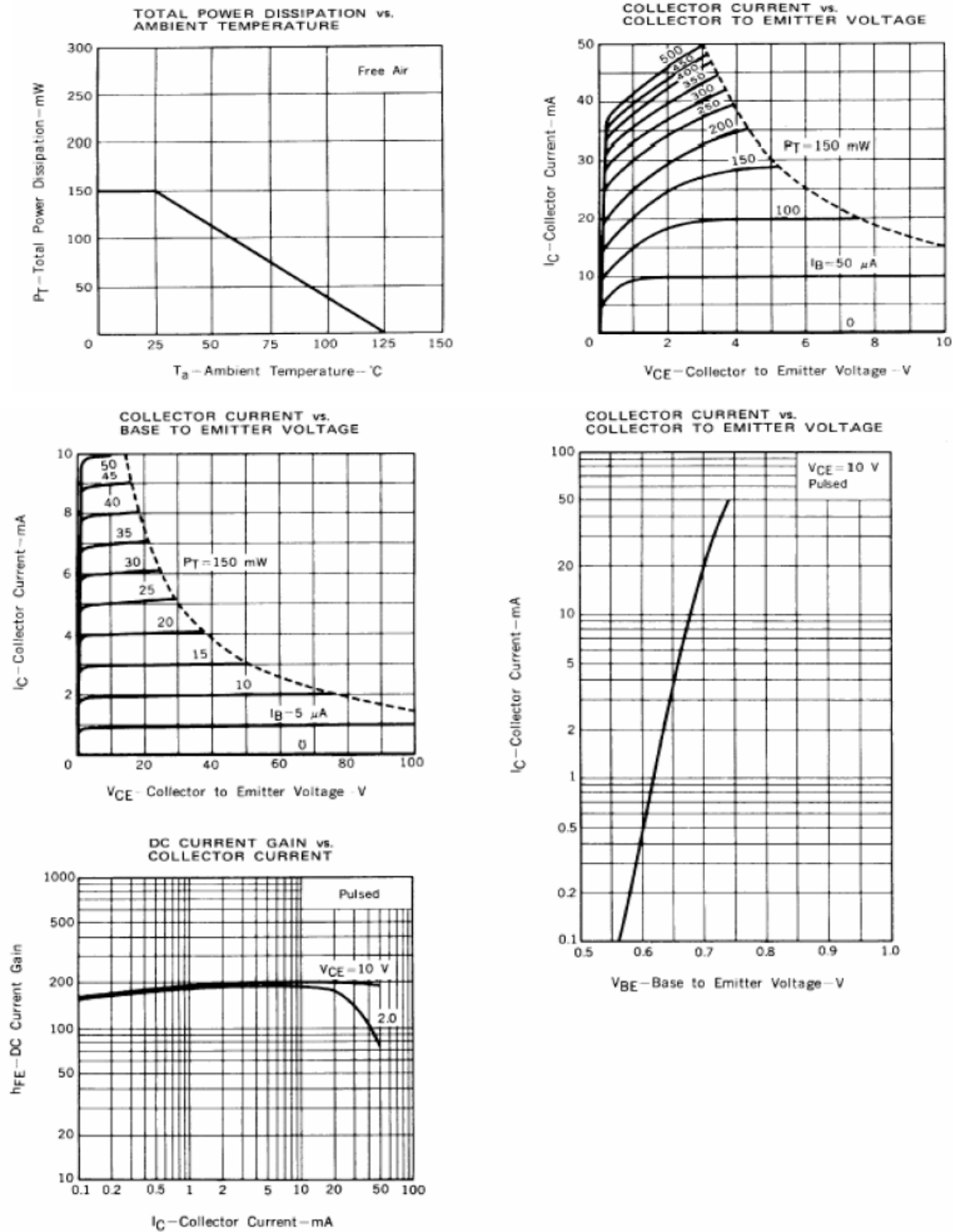
CLASSIFICATION OF $h_{FE(1)}$

Range	90-180	135-270	200-400
Marking	N5	N6	N7

Silicon Epitaxial Planar Transistor

2SC1654

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



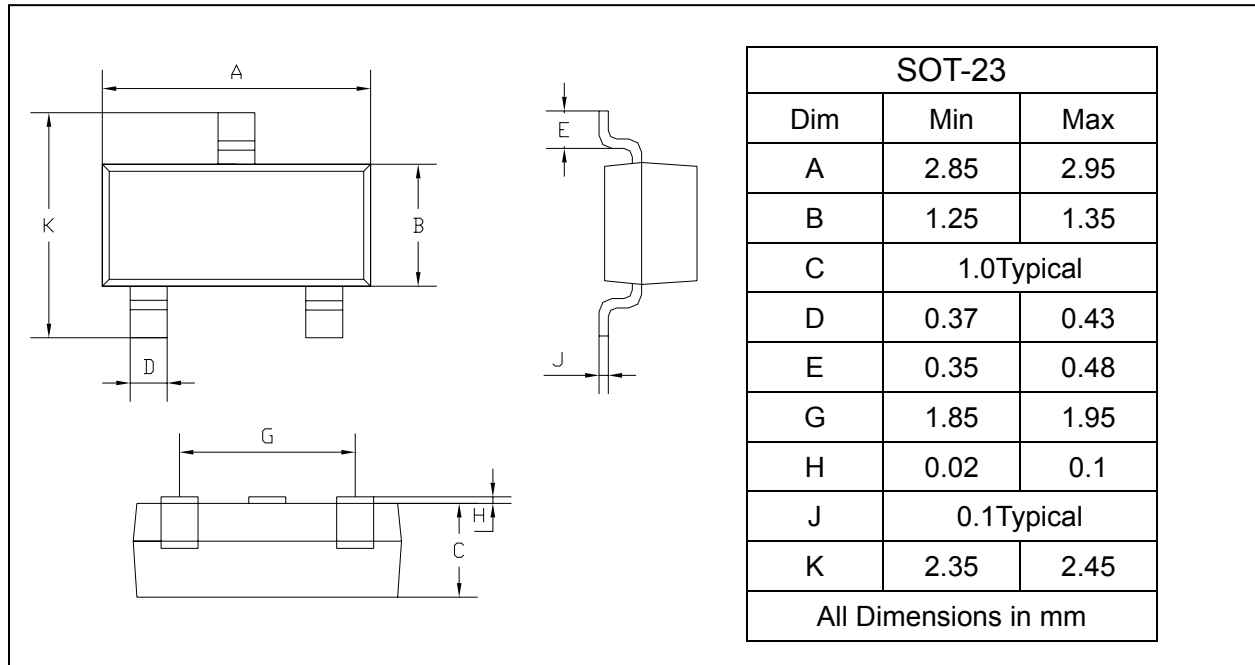
Silicon Epitaxial Planar Transistor

2SC1654

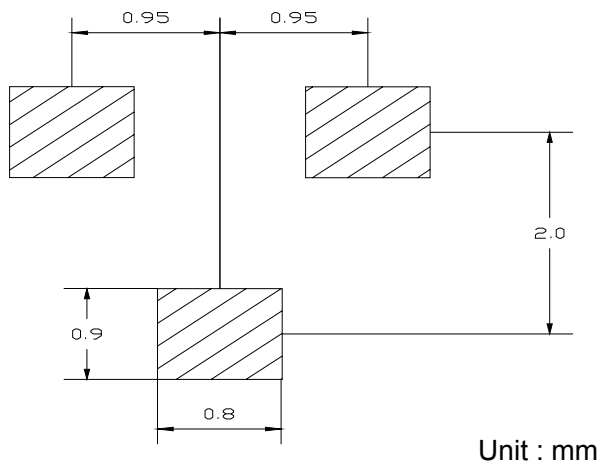
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC1654	SOT-23	3000/Tape&Reel